

HiPerFET™ Power MOSFET

IXFN24N100

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode



$$V_{DSS} = 1000V$$

$$I_{D25} = 24A$$

$$R_{DS(on)} \leq 390m\Omega$$

$$t_{rr} \leq 250ns$$

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	1000	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	1000	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ C$	24	A
I_{DM}	$T_C = 25^\circ C$, pulse width limited by T_{JM}	96	A
I_A	$T_C = 25^\circ C$	24	A
E_{AS}	$T_C = 25^\circ C$	3	J
dV/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$	5	V/ns
P_D	$T_C = 25^\circ C$	568	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	1.6mm (0.062 in.) from case for 10s	300	$^\circ C$
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1mA$	$t = 1min$ $t = 1s$	2500 3000 V~ V~
M_d	Mounting torque Terminal connection torque	1.5/13 1.3/11.5	Nm/lb.in. Nm/lb.in.
Weight		30	g

miniBLOC, SOT-227 B
E153432



G = Gate
S = Source
D = Drain

Either Source terminal at miniBLOC can be used as Main or Kelvin Source

Features

- International standard package
- Encapsulating epoxy meets UL 94 V-0, flammability classification
- miniBLOC with Aluminium nitride isolation
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Avalanche rated
- Low package inductance
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls
- Low voltage relays

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions ($T_J = 25^\circ C$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 3mA$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8mA$	3.0		5.5 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0V$ $T_J = 125^\circ C$			100 μA 2 mA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 12A$, Note 1			390 m Ω

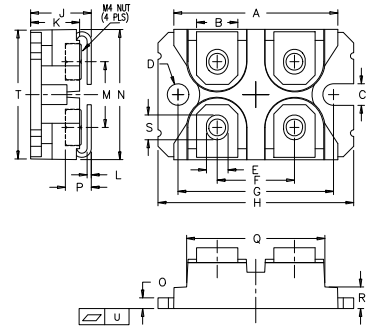
Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10V, I_D = 12A$, Note 1	15	27	S
C_{iss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		8700	pF
C_{oss}			785	pF
C_{rss}			315	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 12A$ $R_G = 1\Omega$ (External)		35	ns
t_r			35	ns
$t_{d(off)}$			75	ns
t_f			21	ns
$Q_{g(on)}$	$V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 12A$		267	nC
Q_{gs}			52	nC
Q_{gd}			142	nC
R_{thJC}			0.22	$^{\circ}C/W$
R_{thCS}		0.05		$^{\circ}C/W$

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0V$			24 A
I_{SM}	Repetitive, pulse width limited by T_{JM}			96 A
V_{SD}	$I_F = 24A, V_{GS} = 0V$, Note 1			1.5 V
t_{rr}	$I_F = 24A, -di/dt = 100A/\mu s$ $V_R = 100V$			250 ns
Q_{RM}			1.0	μC
I_{RM}			8.0	A

Note 1: Pulse test, $t \leq 300\mu s$; duty cycle, $d \leq 2\%$.

SOT-227B Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

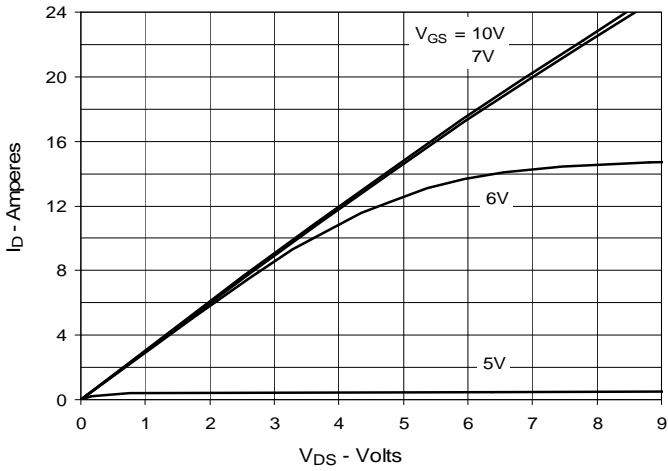
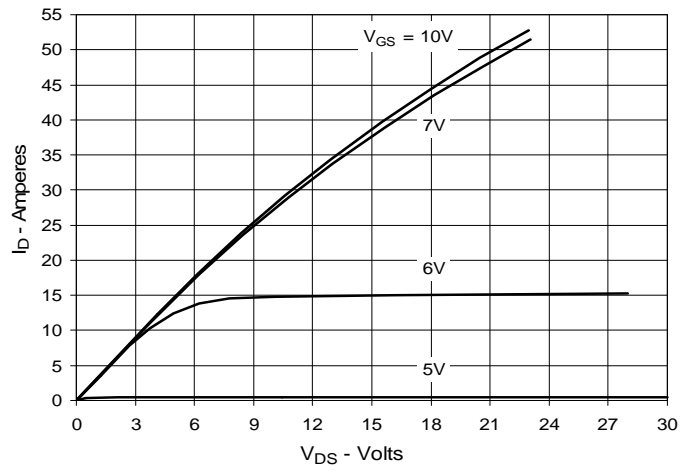
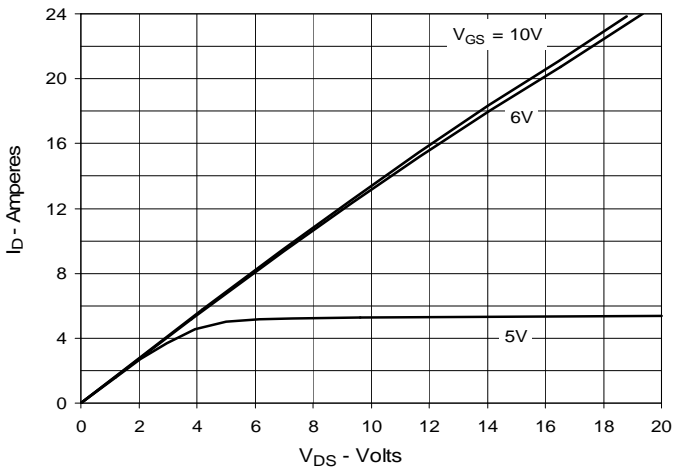
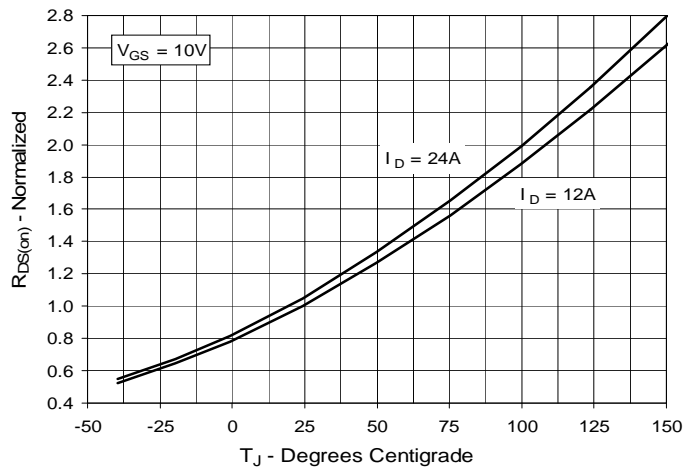
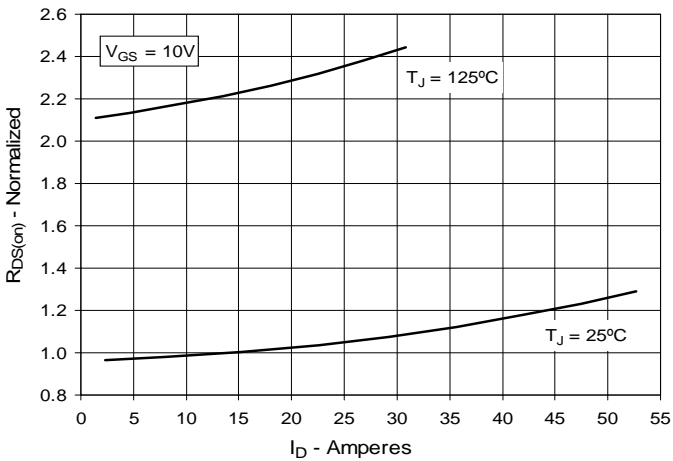
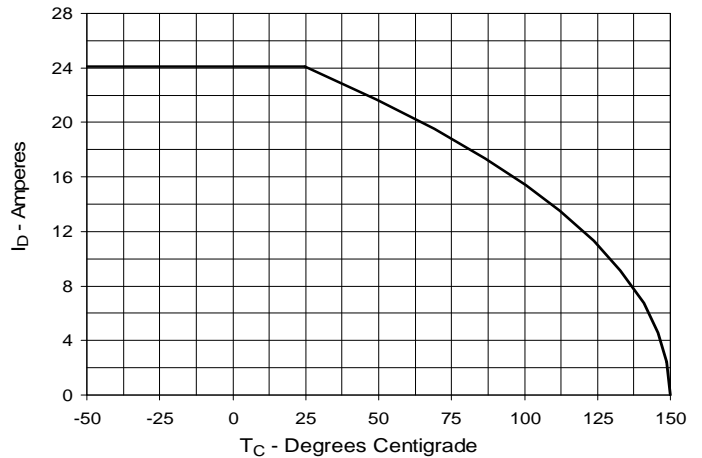
**Fig. 1. Output Characteristics
@ 25°C**

**Fig. 2. Extended Output Characteristics
@ 25°C**

**Fig. 3. Output Characteristics
@ 125°C**

**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 12\text{A}$ Value
vs. Junction Temperature**

**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 12\text{A}$ Value
vs. Drain Current**

**Fig. 6. Maximum Drain Current vs.
Case Temperature**


Fig. 7. Input Admittance

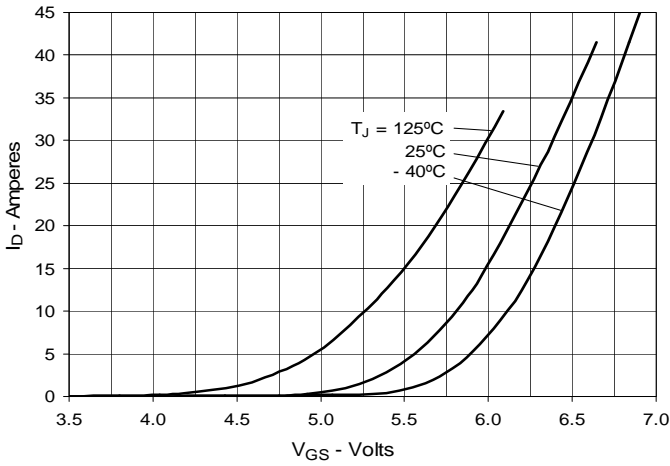


Fig. 8. Transconductance

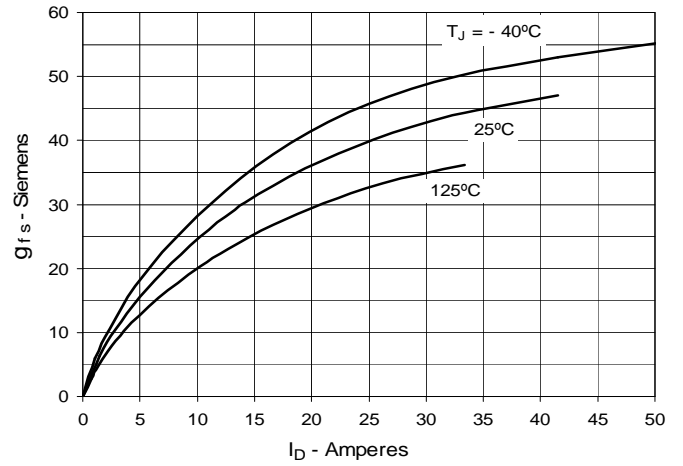


Fig. 9. Forward Voltage Drop of Intrinsic Diode

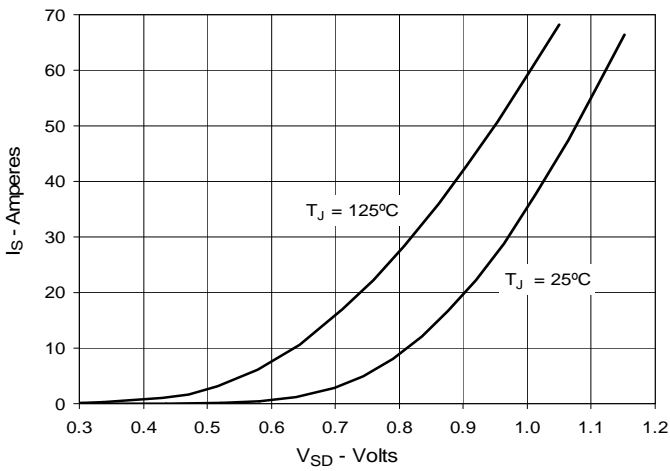


Fig. 10. Gate Charge

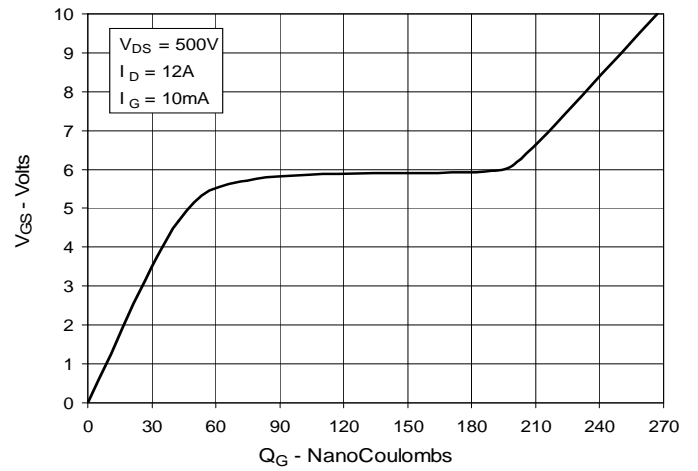


Fig. 11. Capacitance

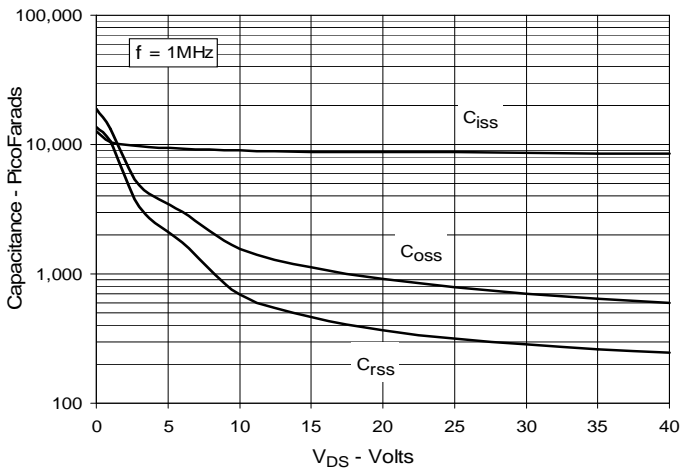
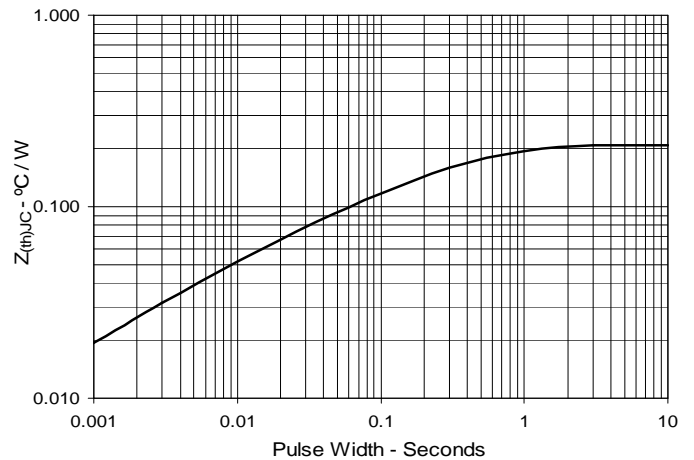


Fig. 12. Maximum Transient Thermal Impedance



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